

MITSUBISHI IGBT

CY20AAJ-8F

Nch IGBT for STROBE FLASHER

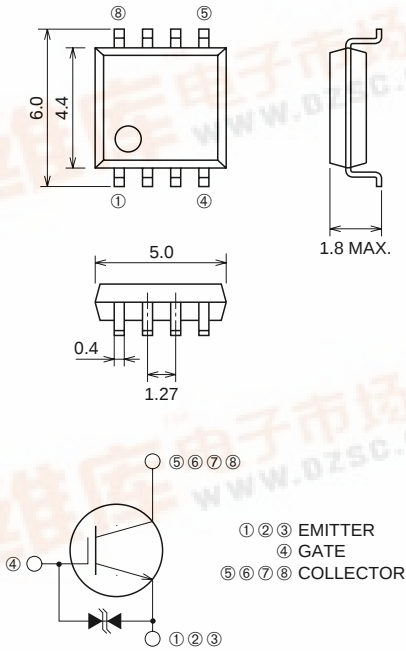
CY20AAJ-8F



- VCES 400V
- ICM 130A
- Drive voltage 4V

OUTLINE DRAWING

Dimensions in mm



SOP-8

APPLICATION

Strobe Flasher for camera

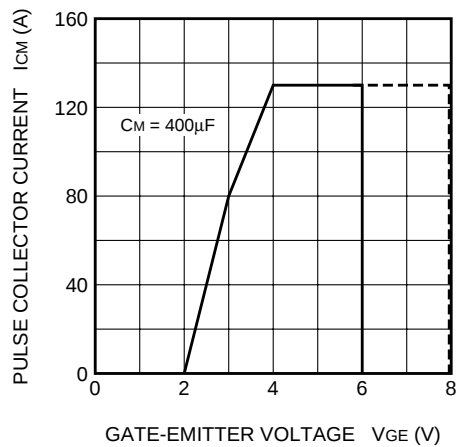
MAXIMUM RATINGS (Tc = 25°C)

Symbol	Parameter	Conditions	Ratings	Unit
VCES	Collector-emitter voltage	VGE = 0V	400	V
VGES	Gate-emitter voltage	VCE = 0V	±6	V
VGEM	Peak gate-emitter voltage	VCE = 0V, tw = 10s	±8	V
ICM	Collector current (Pulsed)	CM = 400μF see figure1	130	A
Tj	Junction temperature		-40 ~ +150	°C
Tstg	Storage temperature		-40 ~ +150	°C

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) CES	Collector-emitter breakdown voltage	$I_C = 1\text{mA}$, $V_{GE} = 0\text{V}$	450	—	—	V
V (BR) GES	Gate-emitter breakdown voltage	$I_G = \pm 100\mu\text{A}$, $V_{CE} = 0\text{V}$	± 8	—	—	V
ICES	Collector-emitter leakage current	$V_{CE} = 400\text{V}$, $V_{GE} = 0\text{V}$	—	—	10	μA
IGES	Gate-emitter leakage current	$V_{GE} = \pm 6\text{V}$, $V_{CE} = 0\text{V}$	—	—	± 10	μA
$V_{GE}(\text{th})$	Gate-emitter threshold voltage	$V_{CE} = 10\text{V}$, $I_C = 1\text{mA}$	—	—	1.5	V

Figure1. MAXIMUM PULSE COLLECTOR CURRENT



APPLICATION EXAMPLE

